

Reg No.: _____

Name: _____

APJ ABDUL KALAM TECHNOLOGICAL UNIVERSITY

B.Tech Degree S8 (R,S) Exam April 2025 (2019 Scheme)

Course Code: ECT448**Course Name: LOW POWER VLSI****Max. Marks: 100****Duration: 3 Hours****PART A***Answer all questions, each carries 3 marks.*

Marks

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| 1 | Explain the hot electron effect with neat diagrams. | (3) |
| 2 | Discuss the design issues in deep submicron transistors. | (3) |
| 3 | Derive the expression for switching power dissipation. | (3) |
| 4 | List various sources of leakage power dissipation. | (3) |
| 5 | List out techniques used for power reduction using supply voltage scaling. | (3) |
| 6 | Discuss about variable threshold CMOS for leakage power reduction. | (3) |
| 7 | List the advantages & disadvantages of clocked circuits. | (3) |
| 8 | Explain the concepts of ratioed logic. | (3) |
| 9 | Explain the difference between adiabatic charging & Conventional charging. | (3) |
| 10 | Draw the circuit diagram of adiabatic amplifier. | (3) |

PART B*Answer any one full question from each module, each carries 14 marks.***Module I**

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| 11 | Explain the MIS structure with neat diagrams when it is
i) Unbiased ii) accumulation iii) depletion iv) strong inversion | (14) |
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OR

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| 12 | Explain the following short channel effects with neat diagrams
i) Drain induced barrier lowering (DIBL) ii) Impact ionization iii) Surface scattering iv) Punch through & discuss the methods to reduce short channel effects. | (14) |
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Module II

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| 13 | Derive the expression for short circuit power dissipation for a CMOS inverter & discuss short current dependency with input and output load. | (14) |
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OR

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| 14 | a) Explain the leakage current mechanisms in short channel transistors. | (8) |
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- b) Explain the formation of glitches in circuits & discuss methods used for eliminating the glitches. (6)

Module III

- 15 a) Describe how transistor stacking is used to reduce leakage current. (6)
b) Explain the term gating. Discuss how clock gating used to reduce power dissipation. (8)

OR

- 16 Explain dynamic & leakage power reduction using transistor sizing. (14)

Module IV

- 17 a) Implement X-OR gate using NMOS & Pseudo NMOS logic. (7)
b) Explain the working of differential current switch logic. (7)

OR

- 18 a) Implement NAND/ AND using DCVS logic & Explain its working with help of a truth table. (8)
b) Explain the working of a dynamic logic circuit. (6)

Module V

- 19 a) Explain the working of Adiabatic logic gate & list out the steps to convert conventional CMOS logic gate to an adiabatic gate. (8)
b) Describe the importance of pulsed power supply in adiabatic logic. (6)

OR

- 20 a) Explain two stage adiabatic buffer & calculate the total energy dissipation in the system. (8)
b) Explain about reversible logic gate structures. (6)
